

ABSTRACT

A memory cell having a source region, a drain region, a source-end control gate, a drain-end control gate, an injection gate arranged between the source-end control gate and the drain-end control gate, a source-end storage element arranged in the source-end control gate, and a drain-end storage element arranged in the drain-end control gate. To program the memory cell, a low electrical voltage is applied to the injection gate, and a high electrical voltage is applied to the control gates.